

Part Number: L-3DP3C

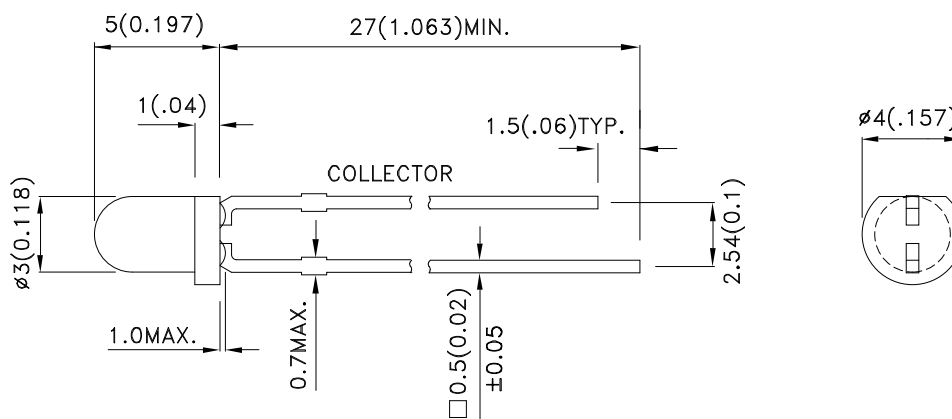
Features

- Mechanically and spectrally matched to the infrared emitting LED lamp.
- Water clear lens.
- RoHS compliant.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.



Electrical / Optical Characteristics at TA=25°C

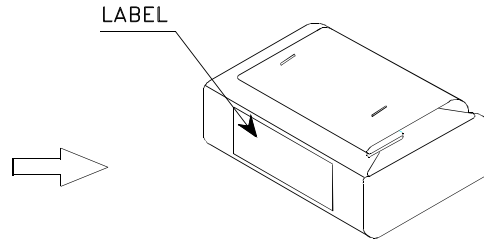
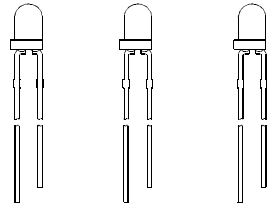
Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage	30			V	I _C =100uA E _e =0mW/c m ²
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage	5			V	I _E =100uA E _e =0mW/c m ²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage			0.8	V	I _C =2mA E _e =20mW/c m ²
I _{CEO}	Collector Dark Current			100	nA	V _{CE} =10V E _e =0mW/c m ²
T _R	Rise Time (10% to 90%)		15		us	V _{CE} = 5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90% to 10%)		15		us	
I _(ON)	On State Collector Current	0.3	0.8		mA	V _{CE} = 5V E _e =1mW/c m ² λ=940nm
2θ1/2	Viewing Angle		50		deg	

Absolute Maximum Ratings at TA=25°C

Parameter	Max.Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature	-40°C To +85°C
Storage Temperature	-40°C To +85°C
Lead Soldering Temperature (>5mm for 5sec)	260°C

PACKING & LABEL SPECIFICATIONS

L-3DP3C

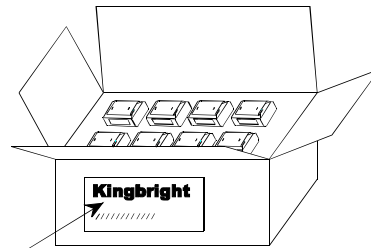
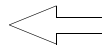


1000PCS / BAG




56K / 9# BOX

OUTSIDE LABEL



OUTSIDE LABEL

28K / 5# BOX

<h1>Kingbright</h1>	
P/NO: L-3Dxxx	
QTY: 1,000 pcs	Q.C. Q C xx xx xxxx PASSED
S/N: XXXX	
CODE: XXX	
LOT NO:	
	
RoHS Compliant	